Low-Voltage CMOS Octal Buffer

With 5 V–Tolerant Inputs and Outputs (3–State, Non–Inverting)

The 74LVC244A is a high performance, non-inverting octal buffer operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows 74LVC244A inputs to be safely driven from 5 V devices. The 74LVC244A is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the output by placing them in a HIGH Z condition.

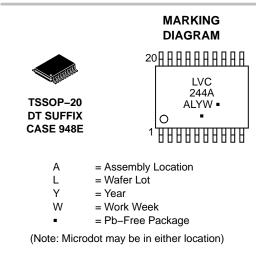
Features

- Designed for 1.2 V to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0$ V
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA) Substantially Reduces System Power Requirements
- ESD Performance:
 - Human Body Model >2000 V
 - Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

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V_{CC}	20E	100	2D0	101	2D1	102	2D2	103	2D3
20	19	18	17	16	15	14	13	12	11
Ĺ									
	2	3	4	5	6	7	8	9	10
10E	1D0	200	1D1	201	1D2	202	1D3	203	GND

Figure 1. Pinout: 20-Lead (Top View)

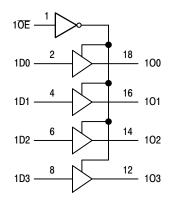
PIN NAMES

PINS	FUNCTION
nOE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3–State Outputs

TRUTH TABLE

INP	UTS	OUTPUTS
10E 20E	1Dn 2Dn	10n, 20n
L	L	L
L	Н	н
Н	Х	Z

H = High Voltage Level L = Low Voltage Level



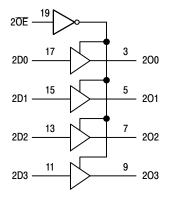


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
VI	DC Input Voltage		$-0.5 \le V_{l} \le +6.5$	V
Vo	DC Output Voltage	Output in 3-State	$-0.5 \le V_O \le +6.5$	V
		Output in HIGH or LOW State (Note 1)	$-0.5 \leq V_O \leq V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
Ι _{ΟΚ}	DC Output Diode Current	V _O < GND	-50	mA
		$V_{O} > V_{CC}$	+50	mA
Ι _Ο	DC Output Source/Sink Current		±50	mA
I _{CC}	DC Supply Current Per Supply Pin		±100	mA
I _{GND}	DC Ground Current Per Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		T _L = 260	°C
ТJ	Junction Temperature Under Bias		T _J = 135	°C
θ_{JA}	Thermal Resistance (Note 2)		110.7	°C/W
MSL	Moisture Sensitivity	Level 1		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Io absolute maximum rating must be observed.
Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3–State	0 0		V _{CC} 5.5	V
I _{ОН}	$ HIGH Level Output Current \\ V_{CC} = 3.0 V - 3.6 V \\ V_{CC} = 2.7 V - 3.0 V $			-24 -12	mA
I _{OL}	$ LOW Level Output Current \\ V_{CC} = 3.0 V - 3.6 V \\ V_{CC} = 2.7 V - 3.0 V $			24 12	mA
T _A	Operating Free–Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	0 0		20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			-4	0°C to +8	5°C	–40°C to +125°C			
Symbol	Parameter	Conditions	Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	Unit
VIH	HIGH-level input	V _{CC} = 1.2 V	1.08	-	-	1.08	-	-	V
	voltage	V _{CC} = 1.65 V to 1.95 V	0.65 x V _{CC}	-	-	0.65 x V _{CC}	-	-	
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	-	
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	-	
V _{IL}	LOW-level input	V _{CC} = 1.2 V	-	-	0.12	-	-	0.12	V
	voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 x V _{CC}	_	-	0.35 x V _{CC}	
		V_{CC} = 2.3 V to 2.7 V	_	-	0.7	-	-	0.7	
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	-	0.8	
V _{OH}	HIGH-level output	$V_{I} = V_{IH} c$	or V _{IL}						V
	voltage	$I_{O} = -100 \ \mu\text{A};$ $V_{CC} = 1.65 \ \text{V} \text{ to } 3.6 \ \text{V}$	V _{CC} - 0.2	-	-	V _{CC} – 0.3	-	-	
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	1.05	-	-	
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	-	
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	-	
		$I_{O} = -18$ mA; $V_{CC} = 3.0$ V	2.4	-	-	2.25	-	-	
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	-	
VOL	LOW-level output	$V_{I} = V_{IH} c$	or V _{IL}						V
	voltage	$I_O = 100 \ \mu A;$ V _{CC} = 1.65 V to 3.6 V	-	-	0.2	_	-	0.3	
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	-	0.65	
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	-	0.8	
		I_{O} = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	-	0.6	
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	-	0.8	
I _I	Input leakage current	$\rm V_{I}$ = 5.5V or GND $\rm V_{CC}$ = 3.6 V	-	±0.1	±5	-	±0.1	±20	μA
I _{OZ}	OFF-state output current	VI = VIH or VIL; V _O = 5.5 V or GND; V _{CC} = 3.6 V	-	±0.1	±5	-	±0.1	±20	μA
I _{OFF}	Power-off leakage current	$V_{1} \text{ or } V_{0} = 5.5 \text{ V}; V_{CC} = 0.0 \text{ V}$	-	±0.1	±10	_	±0.1	±20	μA
I _{CC}	Supply current	$V_{I} = V_{CC} \text{ or } \text{GND}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.6 \text{ V}$	-	0.1	10	_	0.1	40	μA
ΔI_{CC}	Additional supply current	per input pin; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	_	5	500	_	5	5000	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. All typical values are measured at $T_A = 25^{\circ}$ C and $V_{CC} = 3.3$ V, unless stated otherwise.

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AC ELECTRICAL CHARACTERISTICS (t_R = t_F = 2.5 ns)

			-40°C to +85°C -40°C to +125°C				25°C		
Symbol	Parameter	Conditions	Min	Typ1	Max	Min	Typ1	Max	Unit
t _{pd}	Propagation Delay (Note 5)	V _{CC} = 1.2 V	-	17.0	-	-	-	-	ns
	nDn to nOn	V _{CC} = 1.65 V to 1.95 V	1.5	6.4	13.7	1.5	-	15.8	
		V_{CC} = 2.3 V to 2.7 V	1.0	3.4	7.1	1.0	-	8.2	
		V _{CC} = 2.7 V	1.5	3.4	6.9	1.5	-	9.0	
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.5	2.9	5.9	1.5	-	7.5	
t _{en}	Enable Time (Note 6)	V _{CC} = 1.2 V	-	24.0	-	-	-	-	ns
	nOE to nOn	V _{CC} = 1.65 V to 1.95 V	1.5	7.0	17.3	1.5	-	20.0	
		V_{CC} = 2.3 V to 2.7 V	1.5	3.9	9.5	1.5	-	11.0	
		V _{CC} = 2.7 V	1.5	4.1	8.6	1.5	-	11.0	
		V_{CC} = 3.0 V to 3.6 V	1.0	3.2	7.6	1.0	-	9.5	
t _{dis}	Disable Time (Note 7)	V _{CC} = 1.2 V	-	9.0	-	-	-	-	ns
	nOE to nOn	V _{CC} = 1.65 V to 1.95 V	2.2	4.5	9.8	2.2	-	11.3	
		V_{CC} = 2.3 V to 2.7 V	0.5	3.6	5.5	0.5	-	6.4	
		V _{CC} = 2.7 V	1.5	3.3	6.8	1.5	-	8.5	
		V_{CC} = 3.0 V to 3.6 V	1.5	3.1	5.8	1.5	-	7.5	
t _{sk(0)}	Output Skew Time (Note 8)		-	-	1	-	-	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Typical values are measured at TA = 25°C and Vcc = 3.3 V, unless stated otherwise.

5. t_{pd} is the same as t_{PLH} and t_{PHL} .

6. t_{en} is the same as t_{PZL} and t_{PZH} .

7. t_{dis} is the same as t_{PLZ} and t_{PHZ} .

8. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 9)			0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 9)			-0.8 -0.6		V

9. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

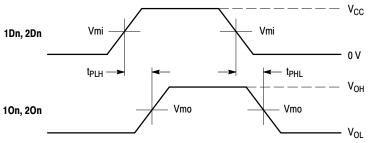
Symbol	Parameter	Condition	Typical	Unit
CIN	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	4	pF
Соит	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	5	pF
C _{PD}	Power Dissipation Capacitance	Per input; V _I = GND or	r V _{CC}	pF
	(Note 10)	V _{CC} = 1.65 V to 1.95 V	6.4	
		V_{CC} = 2.3 V to 2.7 V	9.6	
		V _{CC} = 3.0 V to 3.6 V	12.5	7

10. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

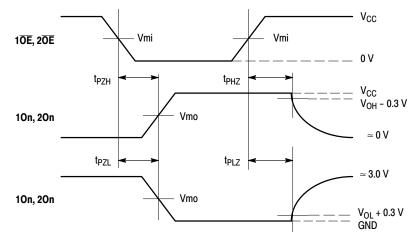
 $\begin{array}{l} \mathsf{P}_{D} = \mathsf{C}_{\mathsf{PD}} \; x \; \mathsf{V}_{\mathsf{CC}}^2 \; x \; \text{fi} \; x \; \mathsf{N} + \Sigma \; (\mathsf{C}_{\mathsf{L}} \; x \; \mathsf{V}_{\mathsf{CC}}^2 \; x \; \text{fo}) \; \text{where:} \\ \mathsf{fi} = \mathsf{input} \; \mathsf{frequency} \; \mathsf{in} \; \mathsf{MHz}; \; \mathsf{fo} = \mathsf{output} \; \mathsf{frequency} \; \mathsf{in} \; \mathsf{MHz} \\ \mathsf{C}_{\mathsf{L}} = \mathsf{output} \; \mathsf{load} \; \mathsf{capacitance} \; \mathsf{in} \; \mathsf{pF} \; \mathsf{V}_{\mathsf{CC}} = \mathsf{supply} \; \mathsf{voltage} \; \mathsf{in} \; \mathsf{Volts} \end{array}$

N = number of outputs switching

 $\Sigma(C_L \times V_{CC}^2 \times fo) = sum of the outputs.$



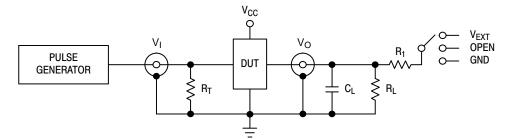




WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns

Figure	3. AC	Waveforms
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		V _{CC}						
Symbol	3.3 V \pm 0.3 V	2.7 V	V _{CC} < 2.7 V					
Vmi	1.5 V	1.5 V	V _{CC} /2					
Vmo	1.5 V	1.5 V	V _{CC} /2					
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V					
V_{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V					



 C_L includes jig and probe capacitance R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$ R_1 = R_L

Supply Voltage	Input		Load		V _{EXT}		
V _{CC} (V)	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
1.65 – 1.95	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
2.3 – 2.7	V _{CC}	≤ 2 ns	30 pF	500 Ω	Open	2 x V _{CC}	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	$2 \times V_{CC}$	GND
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V _{CC}	GND

Figure 4. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
74LVC244ADTR2G	TSSOP–20 (Pb–Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

INCHES

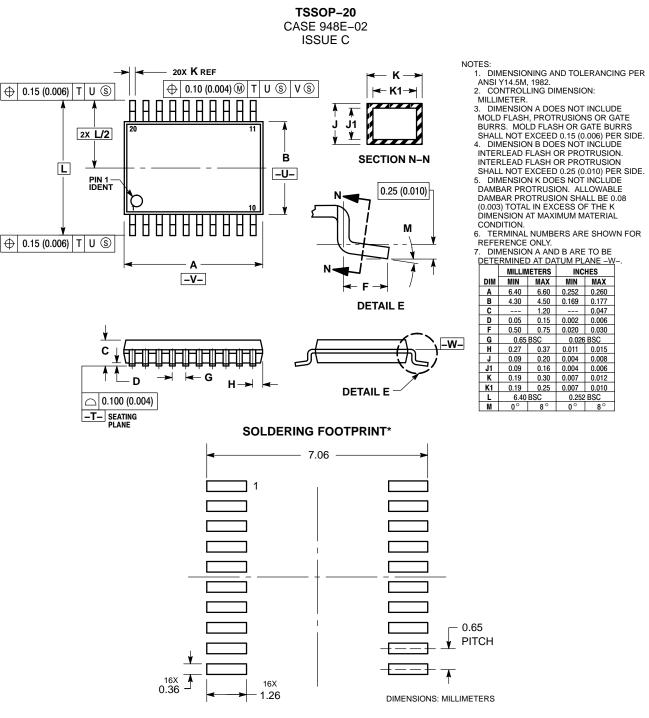
MIN MAX

0.026 BSC

0.252 BSC

0° 8'

0.047



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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